

High Efficiency High Voltage 2A Step Down Converter

1 Features

- Wide 4.2V to 18V Input Voltage Range
- 2A Constant Output Current
- 250μA Low IQ
- 0.765V Reference Voltage
- Integrated 113mΩ / 80mΩ MOSFETs
- 600KHz Switching Frequency
- Internal Soft-Start
- Pulse Frequency Mode at Light Load
- Cycle-by-Cycle Current Limit
- Hiccup Short Circuit Protection
- Thermal Shutdown Protection
- Available in SOT23-6 Package
- RoHS Compliant and Halogen-Free

2 Applications

- Security Cameras
- · Flat Panels and Monitors
- Set Top Boxes and Media Players
- General Purpose

3 Description

The GD30DC1314-I06 is a high efficiency synchronous step-down switching converter. The device operates from an input voltage from 4.2V up to 18V. The main switch and synchronous switch are integrated in the device with very low R_{DS_ON} and capable of delivering up to 2A current.

The switching frequency is set at 600kHz to minimize output voltage ripple. Fault protection includes under voltage lockout, cycle-by-cycle current limit and thermal shutdown.

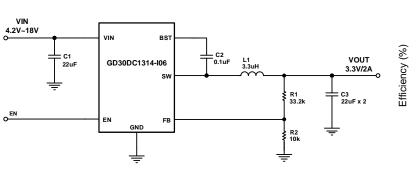
The GD30DC1314-I06 is available with space saving SOT23-6 package and requires minimal number of external components. Together with its low quiescent current, the GD30DC1314-I06 is ideal for security cameras, flat panels and monitors, digital set top boxes etc.

Device Information¹

PART NUMBER	PACKAGE	BODY SIZE (NOM)			
GD30DC1314-I06	SOT23-6	2.92mm x 1.60mm			
1. For packaging details, see <i>Package Information</i> section.					

Simplified Application Schematic

3.3V Output Efficiency



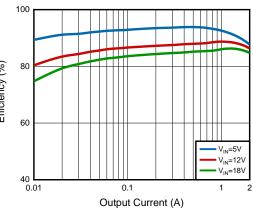




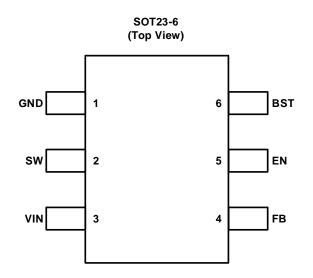
Table of Contents

1	Feat	ures	1
2	Appl	ications	1
3	Desc	ription	1
Tab	le of C	Contents	2
4	Devi	ce Overview	3
	4.1	Pinout and Pin Assignment	3
	4.2	Pin Description	3
5	Para	meter Information	4
	5.1	Absolute Maximum Ratings	4
	5.2	Recommended Operation Conditions	4
	5.3	Electrical Sensitivity	4
	5.4	Thermal Resistance	5
	5.5	Electrical Characteristics	5
	5.6	Typical Characteristics	7
6	Func	tional Description	8
	6.1	Block Diagram	8
	6.2	Operation	8
	6.3	Device Mode Description	10
7	Appl	ication Information	11
	7.1	Typical Application Circuit	11
	7.0		
	7.2	Design Example	11
	7.2 7.3	Design Example Detailed Design Description	
			12
	7.3	Detailed Design Description	12 14
8	7.3 7.4 7.5	Detailed Design Description Power Dissipation	12 14 15
8 9	7.3 7.4 7.5 Layo	Detailed Design Description Power Dissipation Typical Application Curves	12 14 15 19
	7.3 7.4 7.5 Layo	Detailed Design Description Power Dissipation Typical Application Curves	
	 7.3 7.4 7.5 Layo Pack 	Detailed Design Description Power Dissipation Typical Application Curves out Guidelines and Example rage Information	



4 Device Overview

4.1 Pinout and Pin Assignment



4.2 Pin Description

PIN NU	JMBER	PIN	FUNCTION	
NAME	SOT23-6	TYPE ¹		
GND	1	G	Power ground.	
SW	2	0	Switch output. Switch pin connected to the internal MOSFET switches and	
300	2	0	inductor terminal.	
VIN	2	D	Power supply voltage. Operates from a 4.2V to 18V input rail. A decoupling	
VIIN	VIN 3 P		capacitor is required to decouple the input.	
FB	4		Feedback. Feedback pin for the internal control loop. Connect this pin to the	
гв	4	I	external feedback divider.	
EN	5	I	Enable. Pull high to enable the output.	
BST	6	0	Bootstrap. Connect a BST capacitor and a resistor between SW and BST to	
001	0	0	form a floating supply across the high-side switch driver.	

1. I = Input, O = Output, P = Power, G = Ground.



5 Parameter Information

5.1 Absolute Maximum Ratings

Exceeding the operating temperature range(unless otherwise noted)¹

SYMBOL	PARAMETER	MIN	MAX	UNIT
Vin	Input voltage	-0.3	20	V
Ven	Enable pin	-0.3	20	V
\/	Bootstrap voltage	-0.3	25	V
VBST	Bootstrap(vs SW)	-0.3	6.5	V
Maria	Switching node voltage	-0.3	20	V
VSW	V _{sw} Switching node voltage(10ns transient)		22	V
Vfb	Feedback pin	-0.3	6.5	V
TJ	Operating junction temperature	-40	150	°C
T _{stg}	Storage temperature	-65	150	°C

 The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

5.2 Recommended Operation Conditions

SYMBOL ^{1,2}	PARAMETER	MIN	TYP MAX	UNIT
VIN	Input voltage	4.2	18	V
Vout	Output voltage	0.9	VIN * DMAX	V
Іоит	Output current	0	2	А
Vio	I/O pin voltage(EN, FB)	0	5.5	V
TJ	Operating junction temperature	-40	125	°C

1. The device is not guaranteed to function outside of its operating conditions.

2. Refer to the Application Information section for further information.

5.3 Electrical Sensitivity

SYMBOL	CONDITIONS	VALUE	UNIT
V _{ESD(HBM)}	Human-body model (HBM), ANSI/ESDA/JEDEC JS-001-2017 ¹	±2000	V
VESD(CDM)	Charge-device model (CDM), ANSI/ESDA/JEDEC JS-002-2022 ²	±500	V

1. JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

2. JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



5.4 Thermal Resistance

SYMBOL ¹	CONDITIONS	SOT23-6	UNIT
ΘJA	Natural convection, 2S2P PCB	117.71	°C/W
Θјβ	Cold plate, 2S2P PCB	59.55	°C/W
Θ」C	Cold plate, 2S2P PCB	34.00	°C/W
Ψ_{JB}	Natural convection, 2S2P PCB	59.46	°C/W
Ψ_{JT}	Natural convection, 2S2P PCB	2.27	°C/W

1. Thermal characteristics are based on simulation, and meet JEDEC document JESD51-7.

5.5 Electrical Characteristics

 V_{IN} = 12V, T_{J} = 25°C, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
POWER S	UPPLY					
lq	Quiescent current	No switching	179	250	330	μA
ISHDN	Shutdown current	V _{EN} = 0V	2	3	8	μA
Tss	Soft-start time		0.9	1.5	2.0	ms
V _{UVLO}	Under voltage lockout	V _{IN} rising		4		V
VUVLO_HYS	Under voltage lockout hysteresis			330		mV
ENABLE						<u>.</u>
V _{EN_RISE}	Rising enable threshold		1.15	1.20	1.27	V
Ven_hys	Enable threshold hysteresis			150		mV
I _{EN}	Enable input current			2		μA
VOLTAGE	REFERENCE					<u>.</u>
V _{FB}	Feedback voltage	V _{IN} = 4.2 to 18V, T _J =25°C	0.746	0.765	0.784	V
Ifb	Feedback leakage current	T _J = -40°C to 125°C			50	nA
INTEGRA	TED POWER MOSFETS					<u>.</u>
D	High-side FET on resistance			113		mΩ
RDS(on)	Low-side FET on resistance			80		mΩ
SWITCHIN	IG REGULATOR					
Fsw	Switching frequency	V _{FB} = 0.55V		600		KHz
Isw	Switch node leakage current	V _{EN} = 0V, V _{IN} = 12V			10	μA
Ton_min	Minimum on time ¹			58		nS
T _{OFF_MIN}	Minimum off time ¹			120		nS
Izcd	Zero-current detection ¹	Vout = 3.3V, Lo=4.7uH, Iout = 0A		60		mA
DHICCUP	Hiccup duty cycle ¹			25		%
CURRENT	I LIMIT					
ILIM	Valley current limit ¹			3		А



Electrical Characteristics (Continued)

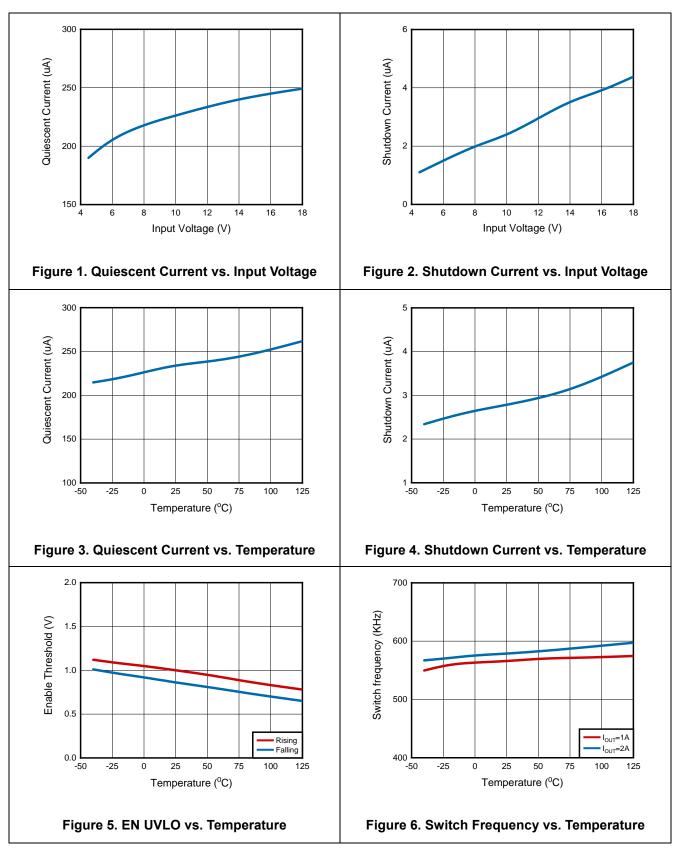
 V_{IN} = 12V, T_J = 25°C, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
THERMAL SHUTDOWM						
T _{TSD}	Thermal shutdown temperature ¹			150		°C
THYS	Thermal shutdown hysteresis ¹			20		°C

1. Guaranteed by design and engineering sample characterization.



5.6 Typical Characteristics





6 Functional Description

6.1 Block Diagram

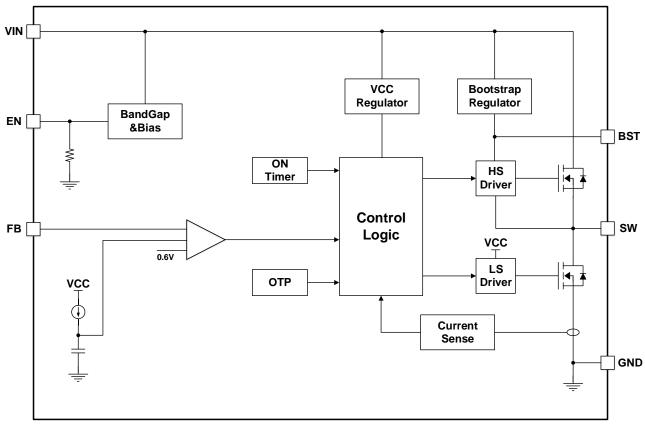


Figure 7. GD30DC1314-I06 Functional Block Diagram

6.2 Operation

The GD30DC1314-I06 is a synchronous switching DC/DC converter with constant on-time control. The adaptive on-time is so controlled by the input/output voltage that the IC operates at relative constant frequency, typically 600kHz. It is capable of delivering up to 2A for VIN between 4.2V and 18V. The output voltage can be as low as 0.9V.

6.2.1 Constant On-Time Control

Based on the V_{OUT}/V_{IN} ratio, a simple circuit sets the required on time for the high-side MOSFET. It makes the switching frequency relatively constant regardless of the variation of input voltage, output voltage, and load current. The relation between t_{ON} and V_{IN} and V_{OUT} is defined as following Equation(1):

$$t_{\rm ON} = \frac{V_{\rm OUT}}{V_{\rm IN}} \times 1.67 {\rm uS}$$
(1)

Excellent load transient response is achieved with a unique fast response constant on-time valley current mode. The switching frequency changes during load transition so that the output voltage comes back in regulation faster than a traditional fixed PWM control scheme. Internal loop compensation is integrated which simplifies the design process while minimizing the number of external components.



6.2.2 Pulse Frequency Modulation

The GD30DC1314-I06 automatically operates with pulse frequency modulation (PFM) at light load currents. As the output current decreases, the GD30DC1314-I06 reduces the switching frequency to maintain high efficiency. When the inductor current reaches zero, the low-side MOSFET turns off. Then the output capacitors offer power for load and feedback resistors.

When feedback voltage(V_{FB}) drops below the reference voltage, the high-side MOSFET is turned on. As the output current increases, the time period that the current modulator regulates becomes shorter, and the high-side MOSFET turns on more frequently. The switching frequency increases in turn. The output current reaches critical levels when the current modulator time is zero, and can be determined with the following Equation(2):

$$I_{OUT} = \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{2 \times L \times f_{SW} \times V_{IN}}$$
(2)

6.2.3 Soft Startup

After enabling the device, internal soft-start circuitry monotonically ramps up the output voltage which reaches nominal output voltage during a soft-start time of 1.5ms (typical). This avoids excessive inrush current and creates a smooth output voltage rise slope.

6.2.4 Pre-Bias Startup

The GD30DC1314-I06 is designed for monotonic start-up into pre-biased loads. If the output is pre-biased to a certain voltage during start-up, the BST voltage is refreshed and charged, and the voltage on the soft start is charged as well. If the BST voltage exceeds its rising threshold voltage, and the soft-start voltage exceeds the sensed output voltage at FB, the part works normally.

6.2.5 Bootstrap Charging

An external bootstrap capacitor can supplies the high-side MOSFET driver. This high-side driver has its own UVLO protection. The rising threshold is 2.2V(typical) and a hysteresis is 150mV(typical).VIN regulates the bootstrap capacitor voltage through a diode. The bootstrap regulator maintain a 4.5V(typical) voltage across BST-SW.

6.2.6 Under Voltage Lockout

To avoid mis-operation of the device at low input voltages, the GD30DC1314-I06 shuts down at voltages lower than 4V(typical) with hysteresis 330mV(typical).

6.2.7 Short Circuit Protection

The device provides short circuit protection function to prevent the device damaged from short condition. When the short condition occurs and the feedback voltage drops lower than 40% of the regulation level, the oscillator frequency will be reduced and hiccup mode will be triggered to prevent the device from overheating during the extended short condition. Once the short condition is removed, the frequency and current limit will return to normal.

6.2.8 Over Current Protection

The device has a 3A(typical) valley current limit control. While the low-side MOSFET is turned on, the conduction



www.gigadevice.com

current is monitored by the internal circuitry. During over current protection(OCP) mode, the inductor valley current is exceeded the low-side source current limit, the high-side MOSFET does not turn on and the low-side MOSFET stays on for the next cycle. The high-side MOSFET turns on again when the inductor valley current is below the low-side sourcing current-limit at the start of a cycle.

6.2.9 Short Circuit Protection

The GD30DC1314-I06 enters short-circuit protection mode when it reaches the current limit and attempts to recover with hiccup mode. In this process, the GD30DC1314-I06 disables the output power stage, discharges the soft-start capacitor, and then attempts to soft-start again automatically. If the short-circuit condition remains after the soft-start ends, the GD30DC1314-I06 repeats this cycle until the short-circuit disappears and the output rises back to regulation level, the hiccup time typically 7ms.

6.2.10 Thermal Shutdown

The internal thermal shutdown circuitry forces the device to stop switching if the junction temperature exceeds 150°C(typical), both the high-side and low-side FETs are turned off. Once the device temperature falls below the threshold with hysteresis 20°C (typical), the device returns to normal operation automatically.

6.3 Device Mode Description

6.3.1 Device Enable

Enable (EN) is a digital control pin that turns the regulator on and off. Drive EN high to turn on the regulator; drive EN low to turn off the regulator. An internal $1M\Omega$ resistor from EN to GND allows EN to be floated to shut down the chip. EN is clamped internally using a 2.8V series Zener diode (see Figure 8). Connecting the EN input through a pull-up resistor to the voltage on VIN limits the EN input current below 100μ A, preventing damage to the Zener diode.

For example, if connection 12V to VIN, then $R_{PULLUP} \ge (12V - 2.8V) / (100K\Omega + 840K\Omega) = 9.8\mu A$

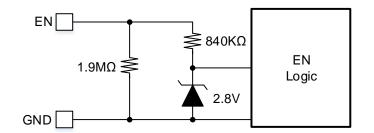


Figure 8. Zener Diode between EN and GND



7 Application Information

The GD30DC1314-I06 device is typically used as a step down converter, which convert an input voltage from 4.2V to 18V to fixed output voltage 3.3V.

7.1 Typical Application Circuit

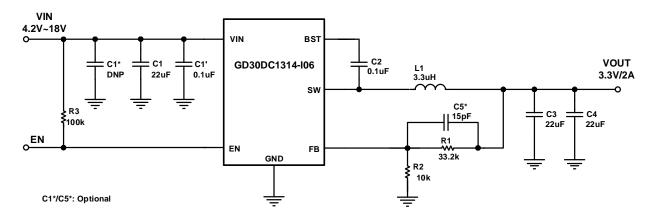


Figure 9. 3.3V, 2A Reference Design

7.2 Design Example

For this design example, use the parameters in Table 1.

Table 1. Design Parameters

PARAMETER	EXAMPLE VALUE
Input Voltage	4.2V to 18V
Output Voltage	3.3V
Maximum Output Current	2A

Table 2 lists the components used for the example.

Table 2. Design Example Component^{1,2}

COMPONENT	DESCRIPTION	
C1,C3,C4	22µF, Ceramic Capacitor, 50V, X7R, size 0805	
C2	0.1µF, Bootstrap Capacitor, 10V, X7R, size 0603	
L1	4.7µH, Power Inductor	
R1,R2,R3	Divider resistor, 1%, size 0603	
C5*	Optional, 15pF if it is needed	

 The components used in these design cases do not belong to GD products, GD does not warrant its accuracy or completeness. GD's customers need to test and verify whether the selected components meet their intended use to ensure stable system operation.

2. Refer to Detailed Design Description section for guidance on component selection and calculation equations.



7.3 Detailed Design Description

7.3.1 Output Voltage Setting

An external resistor divider is used to set output voltage according to Equation(3). By selecting R1 and R2, the output voltage is programmed to the desired value. When the output voltage is regulated, the typical voltage reference at the FB pin is 0.765V.

To ensure system performance, choose the value of R2 carefully. Since a large R2 make FB sensitive to noise and a small R2 increase power loss. So the value of $5K\Omega$ -100K Ω is recommended. It can achieves a balance between system stability and low current consumption.

$$V_{OUT} = 0.765 V \times \left(1 + \frac{R_1}{R_2}\right)$$
(3)

The feedback circuit is shown in Figure 10.

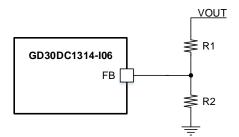


Figure 10. Feedback resistor divider

Table 3 lists the recommended parameters values for common output voltages.

V _{OUT} (V)	R1(KΩ,1%)	R2(KΩ,1%)	L(µH)
5.0	54.9	10	4.7
3.3	33.2	10	3.3
2.5	22.6	10	3.3
1.8	13.7	10	2.2
1.2	5.8	10	2.2
0.9	1.8	10	2.2

7.3.2 Inductor Selection

The inductor selection trade-offs among size, cost, efficiency, and transient response requirements. Three key inductor parameters are specified for operation with the device: inductance value (L), inductor saturation current (ISAT), and DC resistance (DCR). In general, inductors with larger inductance and low DCR values provide much more output and high conversion efficiency, and smaller inductance values can give batter load transient response.

A good compromise between size and loss is to choose the peak-to-peak ripple current equals to 20% to 40% of the IC rated current. And the peak inductor current can be calculated by Equation(4) and Equation(5). Ensure that the peak inductor current is below the maximum switch current.

$$\Delta I_{L} = (0.2 \text{ to } 0.4) \times I_{OUT(MAX)}$$
(4)

$$I_{L(peak)} = I_{OUT(MAX)} + \frac{\Delta I_{L}}{2}$$
(5)

The switching frequency, input voltage, output voltage, and selected inductor ripple current determines the inductor value according to Equation(6). Once an inductor value is chosen, the peak inductor current is determined by Equation(5). Attention that the inductor should not saturate under the inductor peak current.

$$L = \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{V_{IN} \times F_{SW} \times \Delta I_{L}}$$
(6)

7.3.3 Input Capacitor Selection

Input capacitance, C_{IN} , is needed to filter the pulsating current at the drain of the high-side power MOSFET. C_{IN} should be sized to do this without causing a large variation in input voltage. The input capacitance value determines the input voltage ripple of the converter. For most applications, a 10µF capacitor is sufficient.

The peak-to-peak voltage ripple on input capacitor can be estimated with Equation(7):

$$\Delta V_{IN} = \frac{I_{OUT}}{F_{SW} \times C_{IN}} \times \frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)$$
(7)

For best performance, ceramic capacitors with X5R or X7R dielectrics are highly recommended because of their low ESR and small temperature coefficients. To compensate the derating of the ceramic capacitors, the voltage rating of capacitor should be twice of the maximum input voltage. The input capacitor also requires an adequate ripple current rating since it absorbs the input switching current.

The input ripple current can be estimated with Equation(8):

$$I_{CIN} = I_{OUT} \times \sqrt{D \times (1 - D)}$$
(8)

Where D is the duty cycle of converter. The worst-case condition occurs at $V_{IN} = 2V_{OUT}$. At this point, the input ripple current of input capacitance is equal to half of output current. For simplification, choose an input capacitor with an RMS current rating greater than half of the maximum load current.

7.3.4 Output Capacitor Selection

The output capacitor stabilizes the DC output voltage, it directly affects the steady state, output voltage ripple, loop stability, and output voltage overshoot and undershoot during load current transient.

The output voltage ripple can be estimated with Equation(9):

$$\Delta V_{OUT} = \Delta I_{L} \times \left(C_{ESR} + \frac{1}{8 \times F_{SW} \times C_{OUT}} \right)$$
(9)

The output capacitor ripple is essentially composed of two part. One part is caused by the inductor ripple current flowing through the ESR of output capacitors, another part is caused by the inductor ripple current charging and discharging output capacitors. For tantalum or electrolytic capacitors, the ESR dominates the impedance at the



switching frequency. And when using ceramic capacitors, the capacitance dominates the impedance at the switching frequency and causes most of the output voltage ripple.

The output capacitance must be large enough to supply the current when a large load step occurs. But if the output capacitor value is too high, the output voltage will not be able to reach the design value during the soft start time. Two 22µF ceramic capacitors are recommended in this application.

7.4 Power Dissipation

For DC/DC, these is still some power deposited on the chip and converted into heat, in spite of switch mode power supplies have considerably higher efficiency when compared to linear regulators. The device power dissipation includes conduction loss, switching loss, gate charge loss and quiescent current losses. The maximum allowable continuous power dissipation at any ambient temperature is calculated by Equation(10):

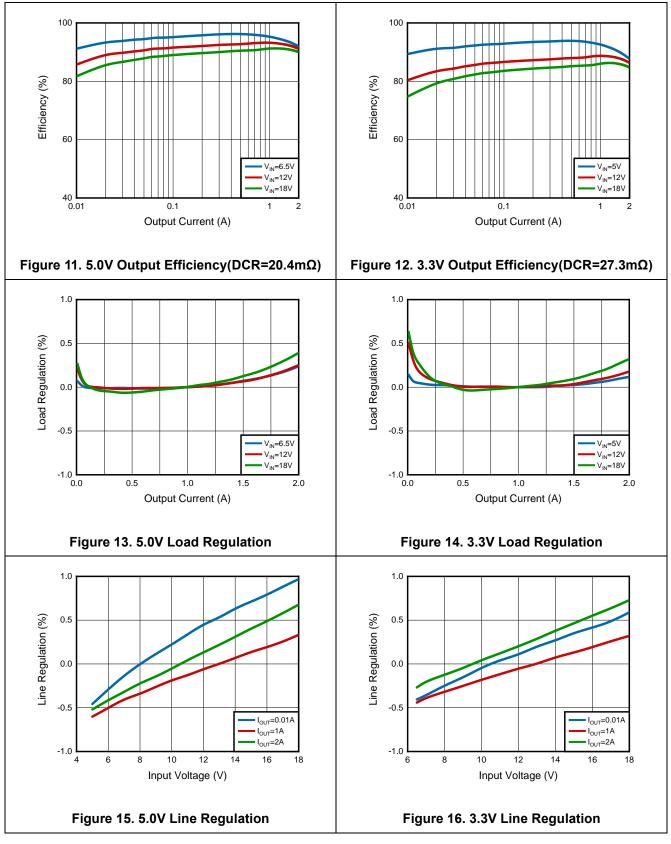
$$\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = \frac{\mathsf{T}_{\mathsf{J}(\mathsf{MAX})} - \mathsf{T}_{\mathsf{A}}}{\theta_{\mathsf{J}\mathsf{A}}} \tag{10}$$

Where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature and θ_{JA} is the junction to ambient thermal resistance. Once exceeding the maximum allowable power, The device enters thermal shutdown to avoid permanent damage.



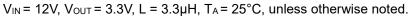
7.5 Typical Application Curves

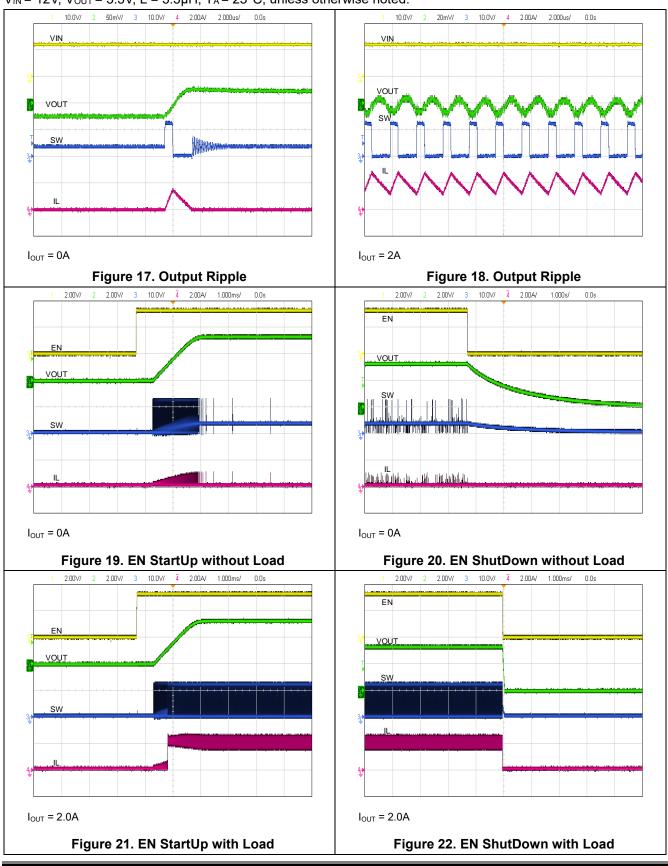






Typical Application Curves (continued)

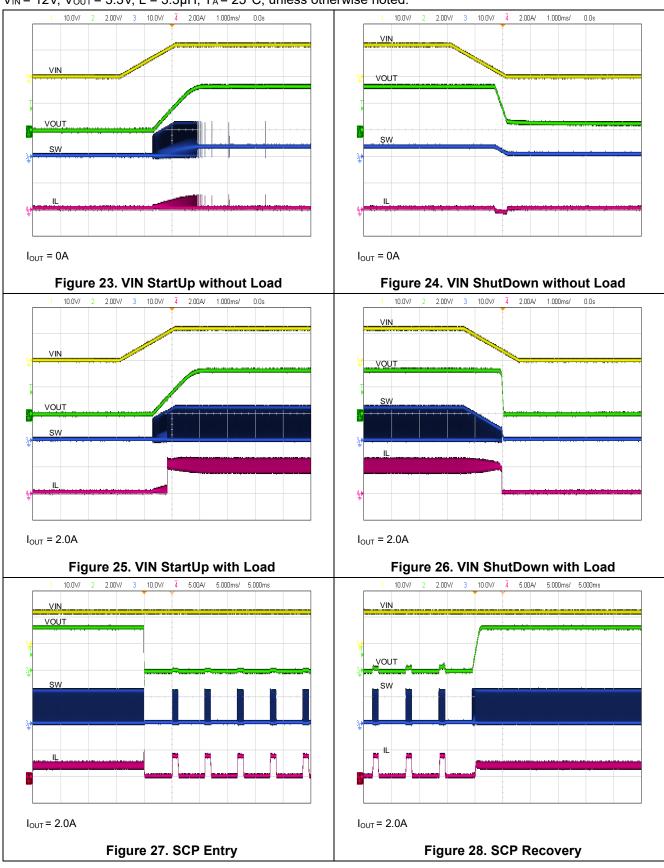






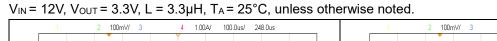
Typical Application Curves (continued)

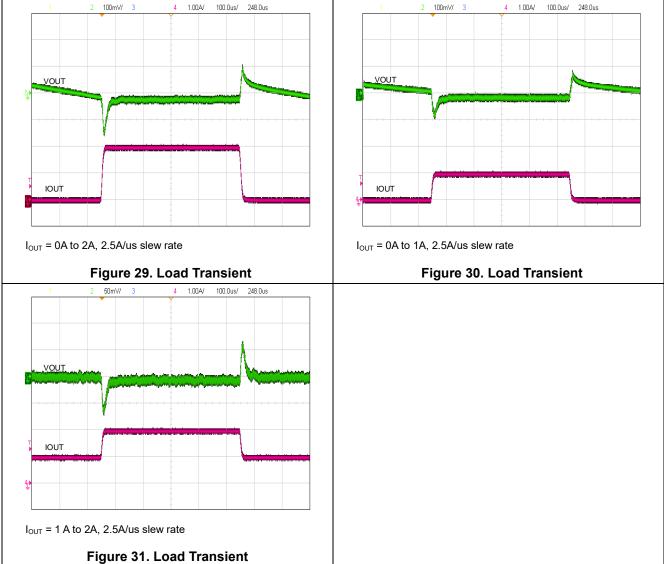
 V_{IN} = 12V, V_{OUT} = 3.3V, L = 3.3µH, T_A = 25°C, unless otherwise noted.





Typical Application Curves (continued)







8 Layout Guidelines and Example

Efficient PCB layout is critical for stable operation. For the high-frequency switching converter, a poor layout design can result in poor line or load regulation and stability issues. For best results, follow the guidelines below.

- 1) Place the high-current paths (GND, IN, and SW) very close to the device with short, direct, and wide traces.
- 2) Place the input capacitor as close to IN and GND as possible.
- 3) Place the external feedback resistors next to FB.
- 4) Keep the switching node SW short and away from the feedback network.
- 5) Keep the VOUT sense line as short as possible or keep it away from the power inductor.

For best results, follow the layout example below.

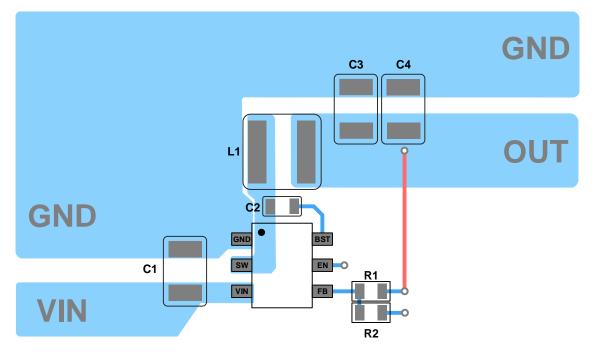
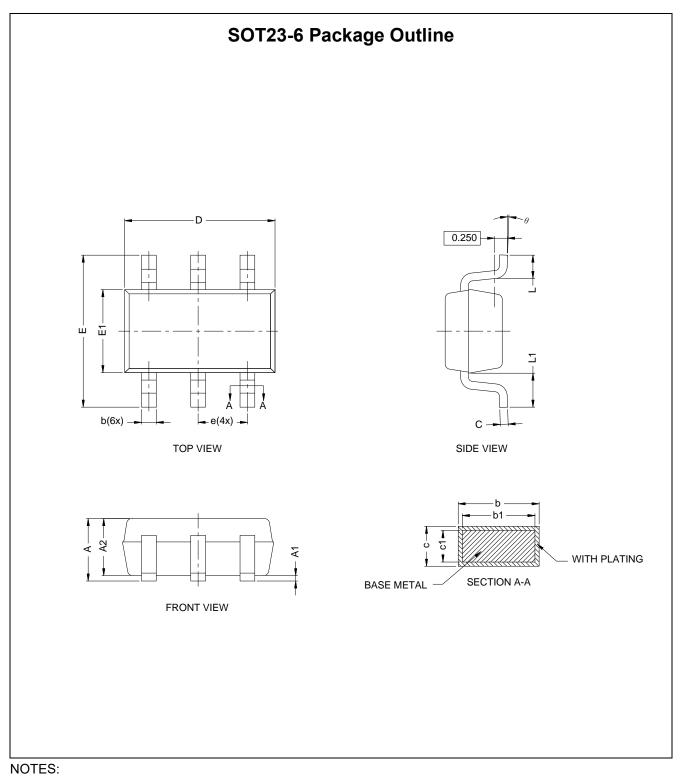


Figure 32. Typical GD30DC1314-I06 Example Layout



9 Package Information

9.1 Outline Dimensions



- 1. All dimensions are in millimeters.
- 2. Package dimensions does not include mold flash, protrusions, or gate burrs.
- 3. Refer to the Table 4 SOT23-6 dimensions(mm).

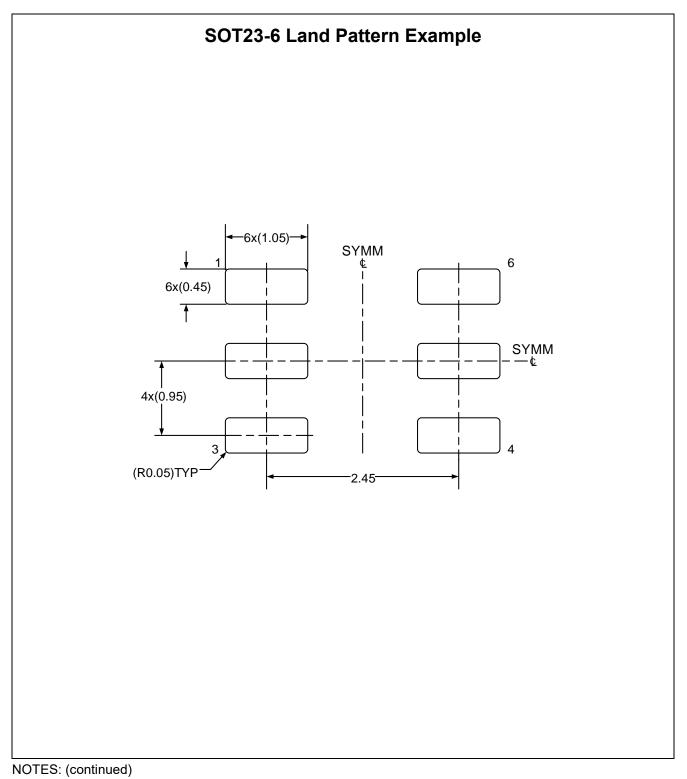


Table 4. SOT23-6 dimensions(mm)

SYMBOL	MIN	NOM	MAX		
A			1.25		
A1	0.04		0.10		
A2	1.00	1.10 1.20			
b	0.38		0.46		
b1	0.37	0.40 0.43			
С	0.13		0.17		
c1	0.12	0.13	0.14		
D	2.82	2.92	3.02		
E	2.60	2.80 3.00			
E1	1.50	1.60	1.70		
е	0.95 BSC				
e1	1.90 BSC				
L	0.30		0.60		
L1	0.60 REF				
θ	0°		8°		



9.2 Recommended Land Pattern



- 1. Refer to the IPC-7351 can also help you complete the designs.
- 2. Exposed metal shown.
- 3. Drawing is 20X scale.



10 Ordering Information

Ordering Code	Package Type	ECO Plan	Packing Type	MOQ	OP Temp(°C)
GD30DC1314SSTR-I06	SOT23-6	Green	Tape & Reel	3000	−40°C to +125°C



Important Notice

This document is the property of GigaDevice Semiconductor Inc. and its subsidiaries (the "Company"). This document, including any product of the Company described in this document (the "Product"), is owned by the Company according to the laws of the People's Republic of China and other applicable laws. The Company reserves all rights under such laws and no Intellectual Property Rights are transferred (either wholly or partially) or licensed by the Company (either expressly or impliedly) herein. The names and brands of third party referred thereto (if any) are the property of their respective owner and referred to for identification purposes only.

The Company makes no representations or warranties of any kind, express or implied, with regard to the merchantability and the fitness for a particular purpose of the Product, nor does the Company assume any liability arising out of the application or use of any Product described in this document. Any information provided in this document is provided only for reference purposes. It is the sole responsibility of the user of this document to determine whether the Product is suitable and fit for its applications and products planned, and properly design, program, and test the functionality and safety of its applications and products planned using the Product. Unless otherwise expressly specified in the datasheet of the Product, the Product is designed, developed, and/or manufactured for ordinary business, industrial, personal, and/or household applications only, and the Product is not designed or intended for use in (i) safety critical applications such as weapons systems, nuclear facilities, atomic energy controller, combustion controller, aeronautic or aerospace applications, traffic signal instruments, pollution control or hazardous substance management; (ii) life-support systems, other medical equipment or systems (including life support equipment and surgical implants); (iii) automotive applications or environments, including but not limited to applications for active and passive safety of automobiles (regardless of front market or aftermarket), for example, EPS, braking, ADAS (camera/fusion), EMS, TCU, BMS, BSG, TPMS, Airbag, Suspension, DMS, ICMS, Domain, ESC, DCDC, e-clutch, advancedlighting, etc.. Automobile herein means a vehicle propelled by a self-contained motor, engine or the like, such as, without limitation, cars, trucks, motorcycles, electric cars, and other transportation devices; and/or (iv) other uses where the failure of the device or the Product can reasonably be expected to result in personal injury, death, or severe property or environmental damage (collectively "Unintended Uses"). Customers shall take any and all actions to ensure the Product meets the applicable laws and regulations. The Company is not liable for, in whole or in part, and customers shall hereby release the Company as well as its suppliers and/or distributors from, any claim, damage, or other liability arising from or related to all Unintended Uses of the Product. Customers shall indemnify and hold the Company, and its officers, employees, subsidiaries, affiliates as well as its suppliers and/or distributors harmless from and against all claims, costs, damages, and other liabilities, including claims for personal injury or death, arising from or related to any Unintended Uses of the Product.

Information in this document is provided solely in connection with the Product. The Company reserves the right to make changes, corrections, modifications or improvements to this document and the Product described herein at any time without notice. The Company shall have no responsibility whatsoever for conflicts or incompatibilities arising from future changes to them. Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2024 GigaDevice - All rights reserved